

Sheikh Ziaur Rahaman

List of Publications by Year in descending order

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28
papers

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567281

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922
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| # | ARTICLE | IF | CITATIONS |
|----|--|-----|-----------|
| 1 | Excellent resistive memory characteristics and switching mechanism using a Ti nanolayer at the Cu/TaO _x interface. <i>Nanoscale Research Letters</i> , 2012, 7, 345. | 5.7 | 78 |
| 2 | Conductive-bridging random access memory: challenges and opportunity for 3D architecture. <i>Nanoscale Research Letters</i> , 2015, 10, 188. | 5.7 | 76 |
| 3 | Bipolar Resistive Switching Memory Using Cu Metallic Filament in Ge _{0.4} Se _{0.6} Solid Electrolyte. <i>Electrochemical and Solid-State Letters</i> , 2010, 13, H159. | 2.2 | 57 |
| 4 | The Role of Ti Buffer Layer Thickness on the Resistive Switching Properties of Hafnium Oxide-Based Resistive Switching Memories. <i>Langmuir</i> , 2017, 33, 4654-4665. | 3.5 | 51 |
| 5 | Temperature-Dependent Non-linear Resistive Switching Characteristics and Mechanism Using a New W/WO ₃ /WO _x /W Structure. <i>Nanoscale Research Letters</i> , 2016, 11, 389. | 5.7 | 43 |
| 6 | Resistive switching memory characteristics of Ge/GeO _x nanowires and evidence of oxygen ion migration. <i>Nanoscale Research Letters</i> , 2013, 8, 220. | 5.7 | 40 |
| 7 | Improved Resistive Switching Memory Characteristics Using Core-Shell IrO _x /Nano-Dots in Al ₂ O ₃ /WO _x Bilayer Structure. <i>Journal of the Electrochemical Society</i> , 2011, 159, H177-H182. | 2.9 | 34 |
| 8 | Nanoscale (EOT = 5.6 nm) nonvolatile memory characteristics using n-Si/SiO ₂ /HfAlO nanocrystal/Al ₂ O ₃ /Ptcapacitors. <i>Nanotechnology</i> , 2008, 19, 435202. | 2.6 | 29 |
| 9 | Enhanced nanoscale resistive switching memory characteristics and switching mechanism using high-Ge-content Ge _{0.5} Se _{0.5} solid electrolyte. <i>Nanoscale Research Letters</i> , 2012, 7, 614. | 5.7 | 29 |
| 10 | Pulse-Width and Temperature Effect on the Switching Behavior of an Etch-Stop-on-MgO-Barrier Spin-Orbit Torque MRAM Cell. <i>IEEE Electron Device Letters</i> , 2018, 39, 1306-1309. | 3.9 | 29 |
| 11 | Understanding of multi-level resistive switching mechanism in GeO _x through redox reaction in H ₂ O ₂ /sarcosine prostate cancer biomarker detection. <i>Scientific Reports</i> , 2017, 7, 11240. | 3.3 | 27 |
| 12 | High- $\hat{\eta}$ Al ₂ O ₃ /WO _x Bilayer Dielectrics for Low-Power Resistive Switching Memory Applications. <i>Japanese Journal of Applied Physics</i> , 2011, 50, 10PH01. | 1.5 | 21 |
| 13 | Scalability and reliability issues of Ti/HfO _x -based 1T1R bipolar RRAM: Occurrence, mitigation, and solution. <i>Applied Physics Letters</i> , 2017, 110, . | 3.3 | 19 |
| 14 | Retention Model of TaO/HfO _x and TaO/AlO _x RRAM with Self-Rectifying Switch Characteristics. <i>Nanoscale Research Letters</i> , 2017, 12, 407. | 5.7 | 16 |
| 15 | Excellent Uniformity and Multilevel Operation in Formation-Free Low Power Resistive Switching Memory Using IrO _x /AlO _x /W Cross-Point. <i>Japanese Journal of Applied Physics</i> , 2012, 51, 04DD10. | 1.5 | 16 |
| 16 | Bipolar Resistive Switching Memory Characteristics Using Al/Cu/GeO _x /W Memristor. <i>ECS Transactions</i> , 2012, 45, 257-261. | 0.5 | 15 |
| 17 | High- $\hat{\eta}$ Al ₂ O ₃ /WO _x Bilayer Dielectrics for Low-Power Resistive Switching Memory Applications. <i>Japanese Journal of Applied Physics</i> , 2011, 50, 10PH01. | 1.5 | 13 |
| 18 | Low power resistive switching memory using Cu metallic filament in Ge _{0.2} Se _{0.8} solid-electrolyte. <i>Microelectronics Reliability</i> , 2010, 50, 643-646. | 1.7 | 12 |

| # | ARTICLE | IF | CITATIONS |
|----|--|-----|-----------|
| 19 | Size-Dependent Switching Properties of Spin-Orbit Torque MRAM With Manufacturing-Friendly 8-Inch Wafer-Level Uniformity. IEEE Journal of the Electron Devices Society, 2020, 8, 163-169. | 2.1 | 12 |
| 20 | Comparison of resistive switching characteristics using copper and aluminum electrodes on GeOx/W cross-point memories. Nanoscale Research Letters, 2013, 8, 509. | 5.7 | 10 |
| 21 | Resistive and New Optical Switching Memory Characteristics Using Thermally Grown Ge _{0.2} Se _{0.8} Film in Cu/GeSex/W Structure. Nanoscale Research Letters, 2015, 10, 392. | 5.7 | 10 |
| 22 | Excellent Uniformity and Multilevel Operation in Formation-Free Low Power Resistive Switching Memory Using IrO _x /AlO _x /W Cross-Point. Japanese Journal of Applied Physics, 2012, 51, 04DD10. | 1.5 | 9 |
| 23 | Record Resistance Ratio and Bipolar/Unipolar Resistive Switching Characteristics of Memory Device Using Germanium Oxide Solid Electrolyte. Japanese Journal of Applied Physics, 2012, 51, 04DD11. | 1.5 | 7 |
| 24 | An 8kb spin-orbit-torque magnetic random-access memory. , 2021, , . | | 6 |
| 25 | Record Resistance Ratio and Bipolar/Unipolar Resistive Switching Characteristics of Memory Device Using Germanium Oxide Solid Electrolyte. Japanese Journal of Applied Physics, 2012, 51, 04DD11. | 1.5 | 3 |
| 26 | Ti/HfO ₂ Based RRAM Operation Voltage Scaling for Embedded Memory. ECS Transactions, 2013, 52, 39-44. | 0.5 | 1 |
| 27 | Effect of Ti buffer layer on HfO _x -based bipolar and complementary resistive switching for future memory applications. , 2016, , . | | 1 |
| 28 | Occurrence and solution to overcome 1stRESET resistance pinning effect in Ti/HfO _x /W based RRAM for low power nonvolatile memory applications. , 2017, , . | | 0 |